

Description

JMT N-channel MOSFET

Features

- $V_{DS}=20V$, $I_D=0.75A$
- $R_{DS(ON)} < 0.38\Omega$ @ $V_{GS} = 4.5V$
 $R_{DS(ON)} < 0.45\Omega$ @ $V_{GS} = 2.5V$
 $R_{DS(ON)} < 0.8\Omega$ @ $V_{GS} = 1.8V$
- N-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive
- Surface Mount Package
- ESD Protected: 2KV

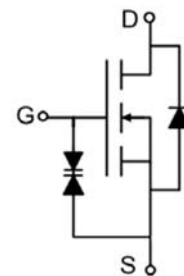
Application

- Battery Protection
- Load Switch
- Power Management

Package



SOT-23



Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	20	V
V_{GSS}	Gate-Source Voltage	± 10	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	0.75
		$T_C = 100^\circ C$	0.5
I_{DM}	Pulsed Drain Current ^{note1}	3	A
P_D	Power Dissipation	$T_A = 25^\circ C$	0.35
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	417	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$



Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = 250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V, V _{GS} = 0V,	-	-	1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±8V	-	-	±10	uA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	0.3	0.65	1	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note2</small>	V _{GS} =4.5V, I _D =0.5A	-	0.25	0.38	Ω
		V _{GS} =2.5V, I _D =0.5A	-	0.35	0.45	
		V _{GS} =1.8V, I _D =0.5A	-	0.4	0.8	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 16V, V _{GS} = 0V, f = 1.0MHz	-	79	120	pF
C _{oss}	Output Capacitance		-	13	20	pF
C _{rss}	Reverse Transfer Capacitance		-	9	15	pF
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} = 10V, I _D =0.5A, R _{GEN} =10Ω, V _{GS} =4.5V,	-	6.7	-	ns
t _r	Turn-on Rise Time		-	4.8	-	ns
t _{d(off)}	Turn-off Delay Time		-	17.3	-	ns
t _f	Turn-off Fall Time		-	7.4	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	0.75	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	3	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S =0.5A	-	0.7	1.3	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

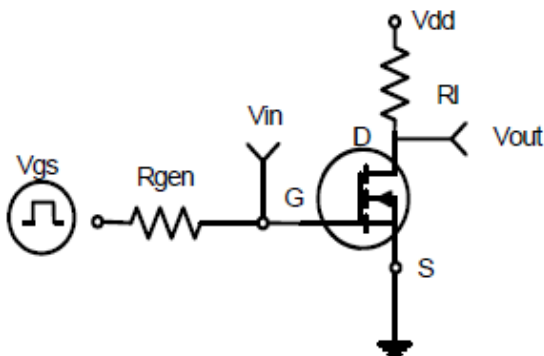


Figure1:Switching Test Circuit

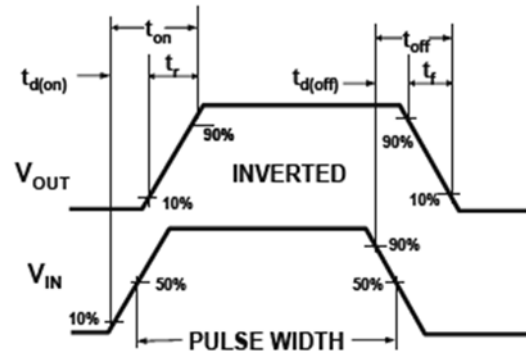
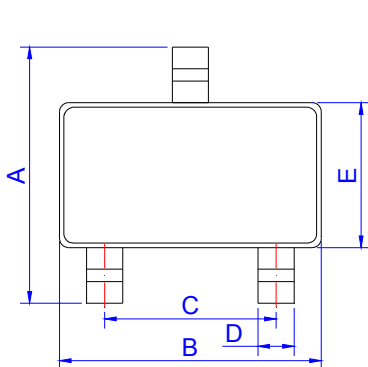
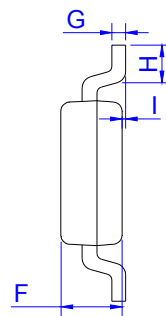


Figure2:Switching Waveforms

Package Mechanical Data

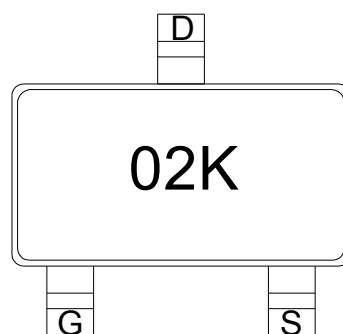


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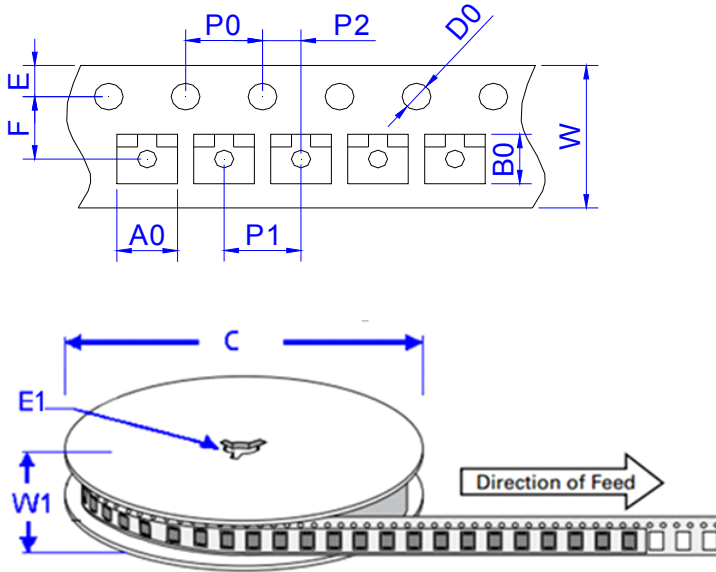
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.30	2.40	2.50	0.091	0.095	0.098
B	2.80	2.90	3.00	0.110	0.114	0.118
C	1.90 REF			0.075 REF		
D	0.35	0.40	0.45	0.014	0.016	0.018
E	1.20	1.30	1.40	0.047	0.051	0.055
F	0.90	1.00	1.10	0.035	0.039	0.043
G		0.10	0.15		0.004	0.006
H	0.20			0.008		
I	0		0.10	0		0.004

Marking



02K:Device Code

Package Information-SOT-23



Ref.	Dimensions	
	Millimeters	Inches
A0	3.15 ± 0.3	0.124 ± 0.012
B0	2.77 ± 0.3	0.109 ± 0.012
C	178	7.0
D0	1.50±0.1	0.059 ± 0.004
E	1.75 ± 0.2	0.069 ± 0.008
E1	13.3±0.3	0.524± 0.012
F	3.5 ± 0.2	0.138 ± 0.008
P0	4.00 ± 0.2	0.157 ± 0.008
P1	4.00 ± 0.2	0.157 ± 0.008
P2	2.00 ± 0.2	0.079 ± 0.008
W	8.00 ± 0.2	0.315 ± 0.008
W1	11.5±1.0	0.453 ± 0.039

Ordering Information-SOT-23

OUTLINE	PACKAGE TYPE	QUANTITY REEL	DESCRIPTION
TAPING	SOT-23	3,000pcs	7 inch reel pack

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